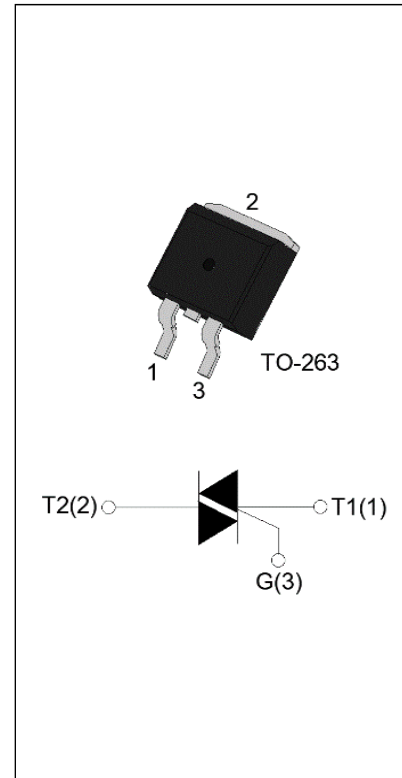


BTB16-800CW**MAIN FEATURES 3Q TRIAC**

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	800	V
$I_{GT1/2/3}$	35/35/35	mA

DESCRIPTION:

The BTB16-800CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. BTB16-800CW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. Package TO-263 is RoHS compliant.

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^{\circ}\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 90^{\circ}\text{C}$)	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle , $t_p=10\text{ms}$, $T_j=25^{\circ}\text{C}$)	I_{TSM}	160	A
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^{\circ}\text{C}$)	I^2t	144	A^2s
Critical rate of rise of on-state current ($T_j=125^{\circ}\text{C}$)	di/dt	50	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^{\circ}\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^{\circ}\text{C}$)	$P_{G(AV)}$	1	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=100\Omega$	I - II -III	MAX.	35	mA
V_{GT}		I - II -III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$ $R_L=100\Omega$	I - II -III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX.	60	mA
		II		100	
I_H	$I_T=500\text{mA}$		MAX.	60	mA
dV/dt	$V_D=2/3V_{DRM}$ $T_j=125^{\circ}\text{C}$		MIN.	500	V/ μs
$(dI/dt)_c$	$T_j=125^{\circ}\text{C}$		MIN.	10	A/ms

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=32\text{A}$	$T_j=25^{\circ}\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.87	V
R_D	Dynamic resistance	$T_j=125^{\circ}\text{C}$	14.6	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	1	mA

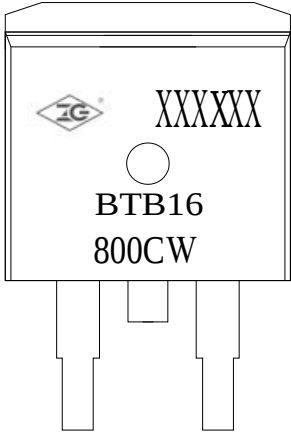
THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.3	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION

BTB16	800	CW
Mode		
800:VDRM/VRRM≥800V		CW:IGT1-3≤35mA

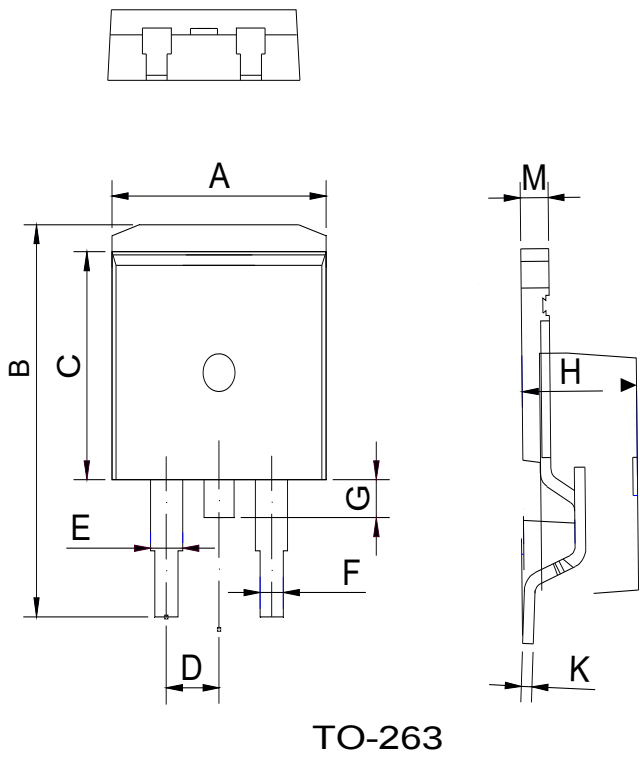
MARKING

	X XX XXX Year Internal Code Week
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ORDERING INFORMATION

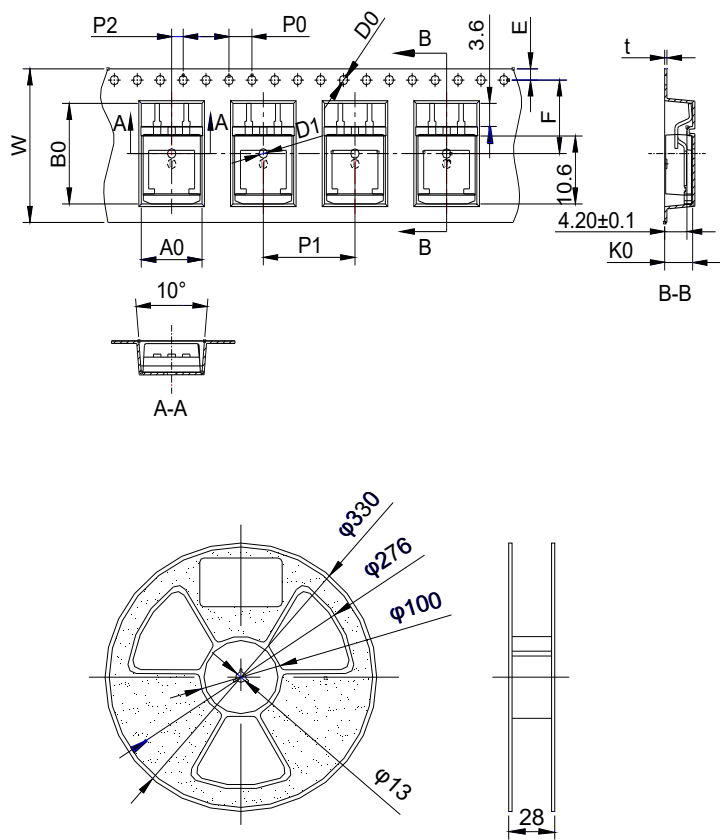
Order code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I -II-III			
BTB16-800CW	800	35	TO-263	800	Tube

PACKAGE MECHANICAL DATA



Ref.	Dimensions		
	Millimeters		
	Min.	Typ.	Max.
A	/	10.00	/
B	13.80	14.20	14.60
C	/	/	1.60
D	/	2.54	/
E	1.20	1.40	1.60
F	0.50	0.70	0.90
G	/	/	1.60
H	/	/	4.80
K	0.30	0.50	0.70
M	1.10	1.30	1.50

DELIVERY MODE



Ref.	Dimensions		
	Millimeters		
	Min.	Typ.	Max.
W	23.70	24.00	24.30
E	1.65	1.75	1.85
F	11.40	11.50	11.60
D0	/	1.50	1.60
D1	/	1.50	1.60
P0	3.90	4.00	4.10
P1	15.90	16.00	16.10
P2	1.90	2.00	2.10
A0	10.80	10.90	11.00
B0	16.20	16.30	16.40
K0	4.80	4.90	5.00
T	0.35	0.40	0.45

PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)
TO-263	TAPING	800	4,000

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

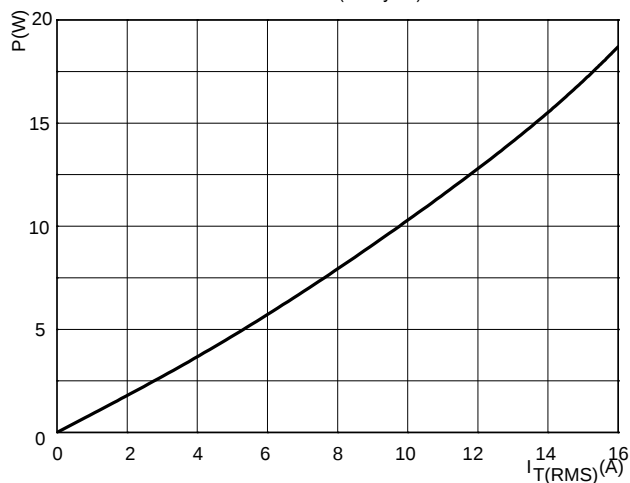


FIG.2: RMS on-state current versus case temperature (full cycle)

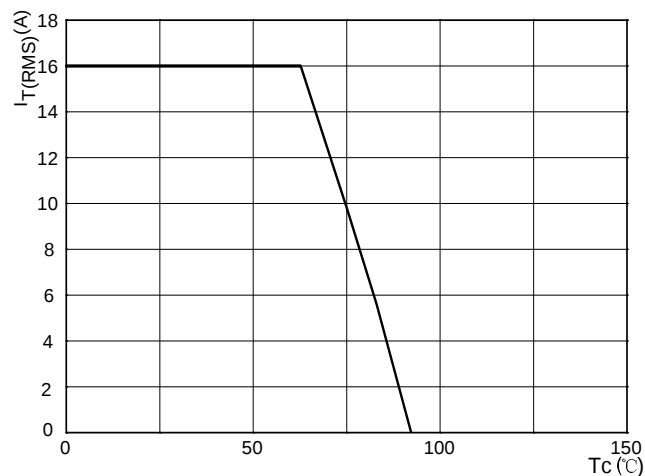


FIG.3: Surge peak on-state current versus number of cycles

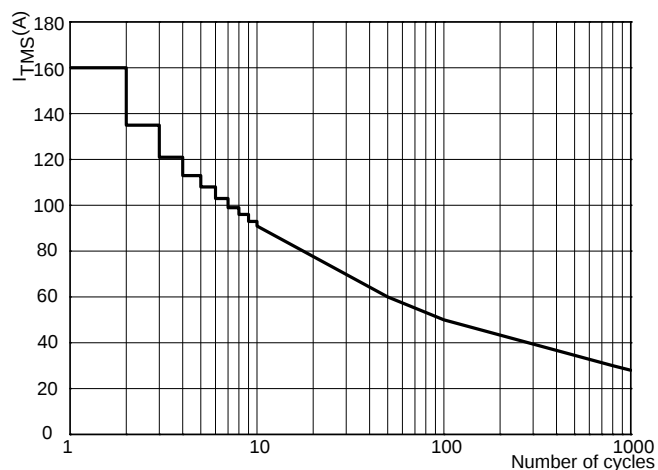


FIG.4: On-state characteristics (maximum values)

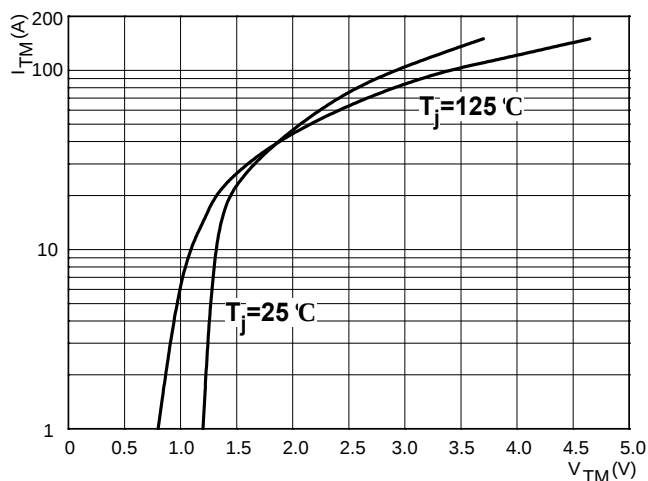
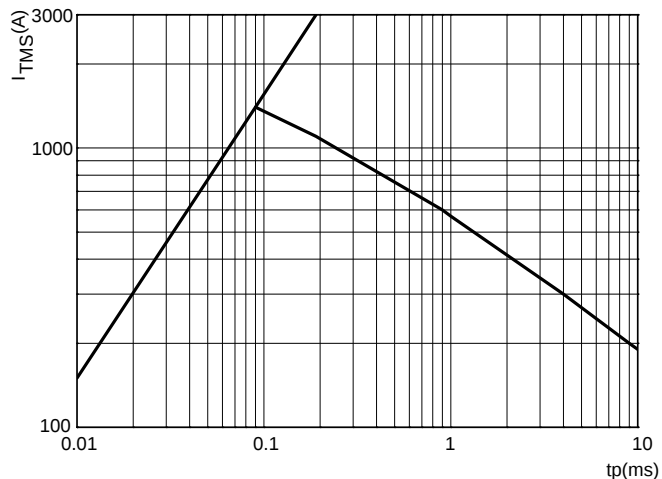
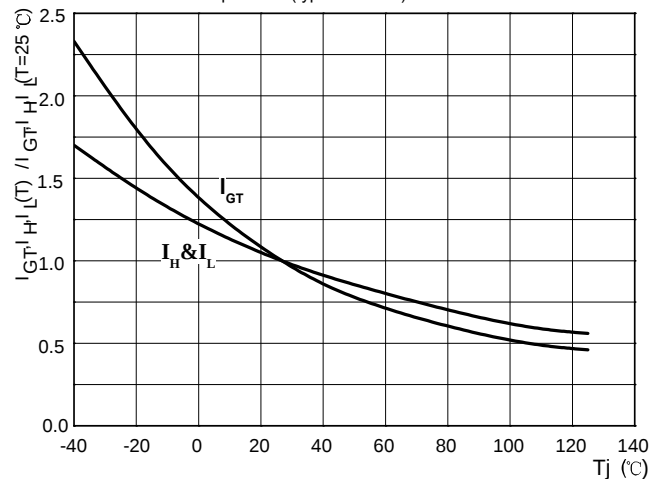
FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$ 

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



单击下面可查看定价，库存，交付和生命周期等信息

[>>ZG\(中鑫半导体\)](#)